

## HIGH EFFICIENCY FAST RECOVERY DIODE

## MAIN PRODUCT CHARACTERISTICS

$I_{F(AV)}$	1 A
$V_{RRM}$	200 V
$t_{rr} (max)$	35 ns

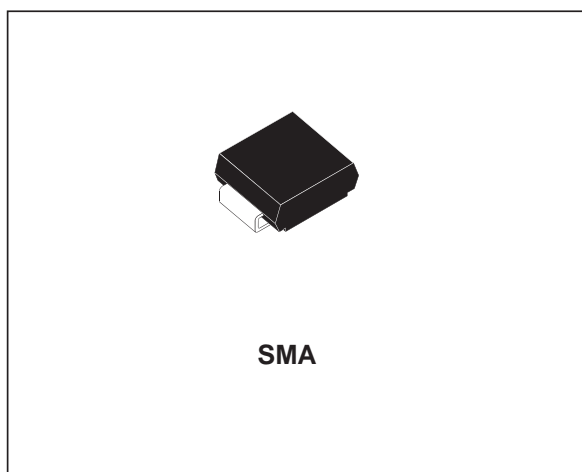
## FEATURES AND BENEFITS

- VERY LOW SWITCHING LOSSES
- LOW FORWARD VOLTAGE DROP
- SURFACE MOUNT DEVICE
- FAST RECTIFIER EPITAXIAL DIODE

## DESCRIPTION

Single chip rectifier suited to Switched Mode Power Supplies and high frequency DC/DC converters.

Packaged in SMA, this surface mount device is intended for use in low voltage, high frequency inverters, free wheeling and polarity protection applications.



## ABSOLUTE RATINGS (limiting values)

Symbol	Parameter		Value	Unit
$V_{RRM}$	Repetitive peak reverse voltage		200	V
$I_{F(RMS)}$	RMS forward current		8	A
$I_{F(AV)}$	Average forward current	$T_{Lead} = 125^{\circ}C$ $\delta = 0.5$	1	A
$I_{FSM}$	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ Sinusoidal	30	A
$T_{stg}$	Storage temperature range		- 65 to + 150	$^{\circ}C$
$T_j$	Maximum junction temperature		150	$^{\circ}C$

## THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
$R_{th(j-l)}$	Junction to lead	30	$^{\circ}C/W$

**STATIC ELECTRICAL CHARACTERISTICS**

Symbol	Tests Conditions	Tests Conditions		Min.	Typ.	Max.	Unit
$I_R^*$	Reverse leakage current	$T_j = 25^\circ\text{C}$	$V_R = V_{RRM}$			3	$\mu\text{A}$
		$T_j = 125^\circ\text{C}$			180	400	
$V_F^{**}$	Forward voltage drop	$T_j = 25^\circ\text{C}$	$I_F = 1\text{ A}$			0.94	V
		$T_j = 150^\circ\text{C}$	$I_F = 1\text{ A}$		0.69	0.74	

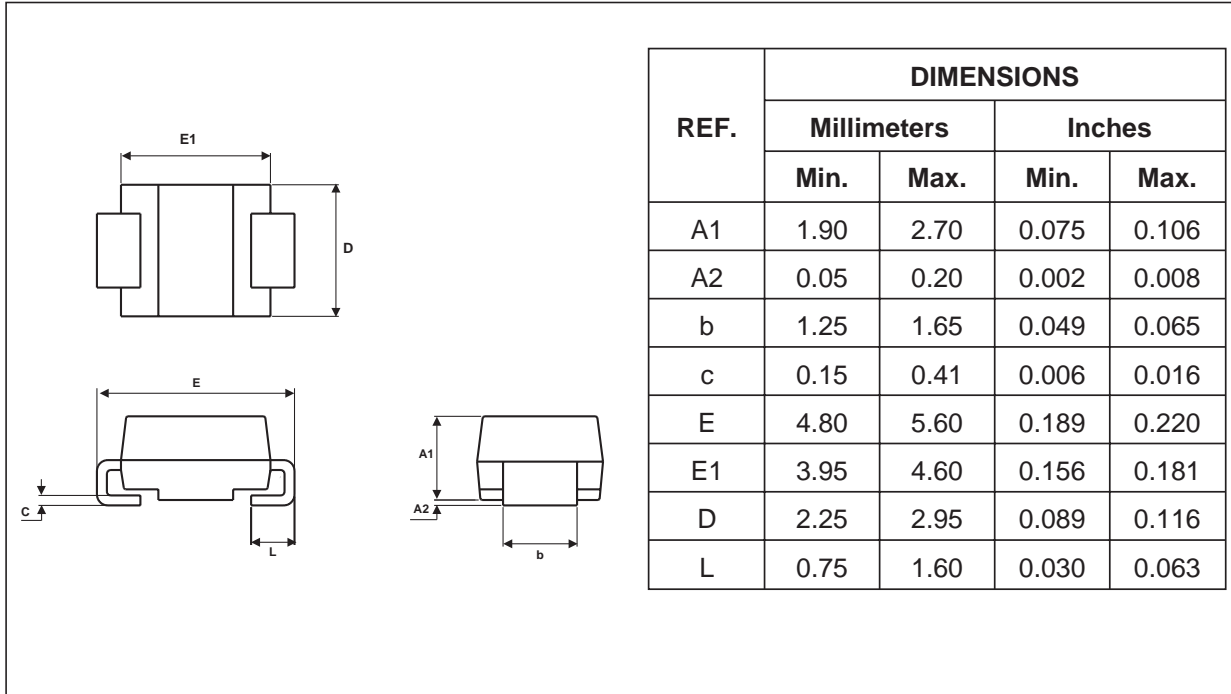
Pulse test : \*  $t_p = 5\text{ms}$ ,  $\delta < 2\%$   
 \*\*  $t_p = 380\ \mu\text{s}$ ,  $\delta < 2\%$

**RECOVERY CHARACTERISTICS**

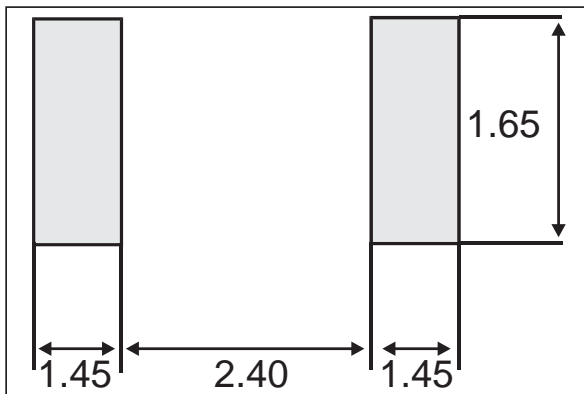
Symbol	Tests Conditions		Min.	Typ.	Max.	Unit
$t_{rr}$	$T_j = 25^\circ\text{C}$	$I_F = 0.50\text{ A}$ $I_{rr} = 0.25\text{ A}$ $I_R = 1\text{ A}$			25	ns
		$I_F = 1\text{ A}$ $di_F/dt = 50\text{ A}/\mu\text{s}$ $V_R = V_{RRM}$		25	35	
$t_{FR}$	$T_j = 25^\circ\text{C}$	$I_F = 1\text{ A}$ $di_F/dt = 100\text{ A}/\mu\text{s}$ Measured at 1 V			25	
$V_{FP}$	$T_j = 25^\circ\text{C}$	$I_F = 1\text{ A}$ $di_F/dt = 100\text{ A}/\mu\text{s}$			5	V

To evaluate the maximum conduction losses use the following equation :  
 $P = 0.62 \times I_{F(AV)} + 0.12 \times I_{F(RMS)}^2$

**PACKAGE MECHANICAL DATA**  
SMA



**FOOT PRINT (in millimeters)**



- **Marking** : R12
- Cathode band is inked
- Epoxy meets UL94-V0
- Weight: 0.06g